

PN4917



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 100 mA. Sourced from Process 66. See 2N3906 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	30	V
V _{EBO}	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	200	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		PN4917	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

PNP General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
0== 0	D.4.0777100				
	RACTERISTICS			1	
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	30		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A}, I_E = 0$	30		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0		V
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \mu\text{A}$	30		V
В	Base Cutoff Current	V _{CE} = 15 V		25	nA
CES	Collector Cutoff Current	V _{CE} = 15 V		25	nA
		V _{CE} = 15 V, T _A = 65 °C		25	μА
	RACTERISTICS*		_	T	,
n _{FE}	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 100 \mu\text{A}$ $V_{CE} = 1.0 \text{ V}, I_{C} = 1.0 m\text{A}$	100 150		
		$V_{CE} = 1.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_{C} = 10 \text{ mA}$	150	300	
		$V_{CE} = 1.0 \text{ V, } I_{C} = 50 \text{ mA}$	30		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 1.0 \text{ mA}, I_B = 0.1 \text{ mA}$		0.13	V
		$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.14 0.30	V
Vagranti	Dogo Emittor Coturation Voltage	$I_C = 3.0 \text{ mA}, I_B = 3.0 \text{ mA}$			V
VRE(eat)	Dase-Emilier Saturation voltage	$I_C = I.U IIIA, I_B = U.I IIIA$		0.75	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$	0.70	0.75	V
V _{BE(sat)}	base-Emilier Saturation voltage	, ,	0.70 0.75		
		$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		0.90	V
	IGNAL CHARACTERISTICS Output Capacitance	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		0.90	V
SMALL S	IGNAL CHARACTERISTICS	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.90 1.10	V V
SMALL S	IGNAL CHARACTERISTICS Output Capacitance	$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$ $V_{CB} = 10 \text{ V}, f = 1.0 \text{ MHz}$		0.90 1.10	V V
SMALL S	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 10 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ \end{split}$ $\begin{split} V_{CE} &= 20 \text{ V, } I_C = 10 \text{ mA} \\ f &= 80 \text{ MHz} \end{split}$	0.75	0.90 1.10	V V
SMALL S Cob Cib	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 10 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ \end{split}$ $\begin{split} I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ \end{split}$ $\begin{split} V_{CE} &= 20 \text{ V, } I_C = 10 \text{ mA} \\ f &= 80 \text{ MHz} \\ \end{split}$ $\begin{split} V_{CE} &= 5.0 \text{ V, } I_C = 1.0 \text{ mA, } \\ R_S &= 100 \Omega, f = 100 \text{ MHz} \\ \end{split}$	0.75	0.90 1.10 4.5 8.0	PF PF
SMALL S	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Collector-Base Time Constant	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 10 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ \end{split}$ $\begin{split} V_{CE} &= 20 \text{ V, } I_C = 10 \text{ mA} \\ f &= 80 \text{ MHz} \\ \end{split}$ \end{split} $V_{CE} &= 5.0 \text{ V, } I_C = 1.0 \text{ mA, } \end{split}$	0.75	0.90 1.10 4.5 8.0	pF pF
SMALL S C _{ob} C _{ib} Ofe tb'Cc	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Collector-Base Time Constant Noise Figure	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 10 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ \end{split}$ $\begin{split} I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ \end{split}$ $\begin{split} V_{CE} &= 20 \text{ V, } I_C = 10 \text{ mA} \\ f &= 80 \text{ MHz} \\ \end{split}$ $\begin{split} V_{CE} &= 5.0 \text{ V, } I_C = 1.0 \text{ mA, } \\ R_S &= 100 \Omega, f = 100 \text{ MHz} \\ V_{CE} &= 5.0 \text{ V, } I_C = 100 M, \end{split}$	0.75	0.90 1.10 4.5 8.0 50	pF pF ps dB
SMALL S Cob Cib Ofe tb'Cc	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Collector-Base Time Constant Noise Figure	$\begin{split} &I_C = 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ &I_C = 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{aligned} &V_{CB} = 10 \text{ V, } f = 1.0 \text{ MHz} \\ &V_{EB} = 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ &I_C = 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ &f = 100 \text{ MHz} \\ \end{aligned}$ $\begin{aligned} &V_{CE} = 20 \text{ V, } I_C = 10 \text{ mA} \\ &f = 80 \text{ MHz} \\ \end{aligned}$ $\begin{aligned} &V_{CE} = 5.0 \text{ V, } I_C = 1.0 \text{ mA, } \\ &R_S = 100 \Omega, f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V, } I_C = 100 \text{ mA, } \\ &R_S = 1.0 \text{ k}\Omega \end{aligned}$	0.75	0.90 1.10 4.5 8.0 50	pF pF ps dB
SMALL SI Cob Cib Ofe tb'Cc NF	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Collector-Base Time Constant Noise Figure NG CHARACTERISTICS Turn-on Time	$\begin{split} &I_C = 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ &I_C = 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $&V_{CB} = 10 \text{ V, } f = 1.0 \text{ MHz} \\ &V_{EB} = 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ &I_C = 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ &f = 100 \text{ MHz} \\ \end{split}$ $&V_{CE} = 20 \text{ V, } I_C = 10 \text{ mA} \\ &f = 80 \text{ MHz} \\ \end{aligned}$ $&V_{CE} = 5.0 \text{ V, } I_C = 1.0 \text{ mA, } \\ &R_S = 100 \Omega, f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V, } I_C = 100 \mu\text{A, } \\ &R_S = 1.0 k\Omega \\ \end{split}$ $&V_{CC} = 10 \text{ V, } I_C = 50 \text{ mA, } \\ \end{split}$	0.75	0.90 1.10 4.5 8.0 50 6.0 4.0	pF pF ps dB dB
SMALL Si Cob Cib Ofe Ob'Cc NF SWITCHII	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Collector-Base Time Constant Noise Figure NG CHARACTERISTICS Turn-on Time Delay Time	$\begin{split} &I_C = 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ &I_C = 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{aligned} &V_{CB} = 10 \text{ V, } f = 1.0 \text{ MHz} \\ &V_{EB} = 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ &I_C = 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ &f = 100 \text{ MHz} \\ \end{aligned}$ $\begin{aligned} &V_{CE} = 20 \text{ V, } I_C = 10 \text{ mA} \\ &f = 80 \text{ MHz} \\ \end{aligned}$ $\begin{aligned} &V_{CE} = 5.0 \text{ V, } I_C = 1.0 \text{ mA, } \\ &R_S = 100 \Omega, f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V, } I_C = 100 \text{ mA, } \\ &R_S = 1.0 \text{ k}\Omega \end{aligned}$	0.75	0.90 1.10 4.5 8.0 50 6.0 4.0	pF pF ps dB dB
SMALL S Cob Cib Ofe rb'Cc NF SWITCHII	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Collector-Base Time Constant Noise Figure NG CHARACTERISTICS Turn-on Time Delay Time Rise Time	$\begin{split} &I_C = 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ &I_C = 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $&V_{CB} = 10 \text{ V, } f = 1.0 \text{ MHz} \\ &V_{EB} = 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ &I_C = 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ &f = 100 \text{ MHz} \\ &V_{CE} = 20 \text{ V, } I_C = 10 \text{ mA} \\ &f = 80 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V, } I_C = 1.0 \text{ mA, } \\ &R_S = 100 \Omega, f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V, } I_C = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V, } I_C = 100 \text{ MA, } \\ &R_S = 1.0 \text{ k}\Omega \\ \end{split}$ $&V_{CC} = 10 \text{ V, } I_C = 50 \text{ mA, } \\ &I_{B1} = 5.0 \text{ mA} \\ \end{split}$	0.75	0.90 1.10 4.5 8.0 50 6.0 4.0 40 15 40	pF pF dB dB ns ns ns
SMALL SI Cob Cib Ofe tb'Cc NF	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Collector-Base Time Constant Noise Figure NG CHARACTERISTICS Turn-on Time Delay Time	$\begin{split} &I_C = 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ &I_C = 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $&V_{CB} = 10 \text{ V, } f = 1.0 \text{ MHz} \\ &V_{EB} = 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ &I_C = 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ &f = 100 \text{ MHz} \\ \end{split}$ $&V_{CE} = 20 \text{ V, } I_C = 10 \text{ mA} \\ &f = 80 \text{ MHz} \\ \end{aligned}$ $&V_{CE} = 5.0 \text{ V, } I_C = 1.0 \text{ mA, } \\ &R_S = 100 \Omega, f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V, } I_C = 100 \mu\text{A, } \\ &R_S = 1.0 k\Omega \\ \end{split}$ $&V_{CC} = 10 \text{ V, } I_C = 50 \text{ mA, } \\ \end{split}$	0.75	0.90 1.10 4.5 8.0 50 6.0 4.0	pF pF dB dB ns

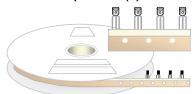
^{*}Pulse Test: Pulse Width≤300 μs, Duty Cycle≤2.0%

TO-92 Tape and Reel Data FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z 2,000 D75Z **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON BOTTOM

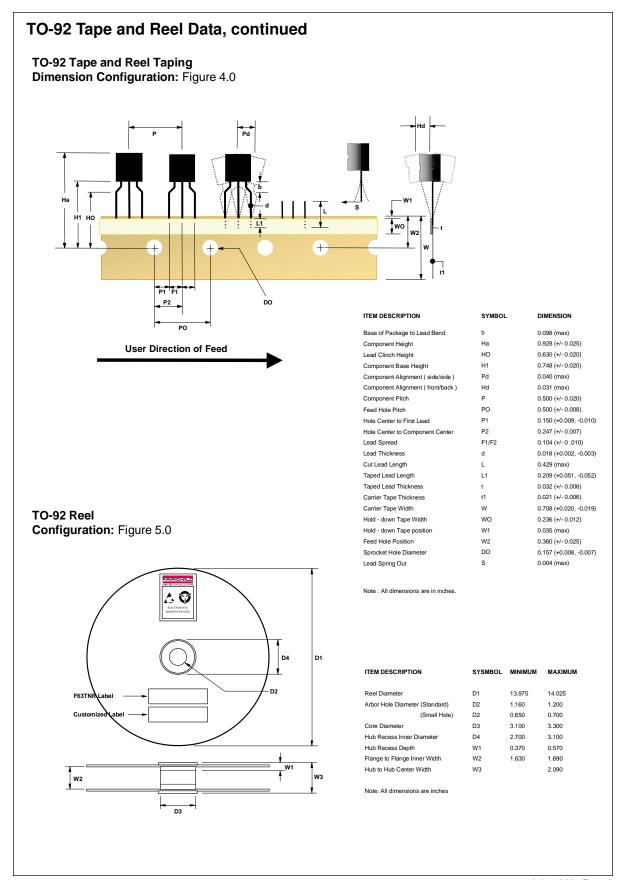
Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0





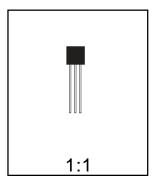


TO-92 Package Dimensions



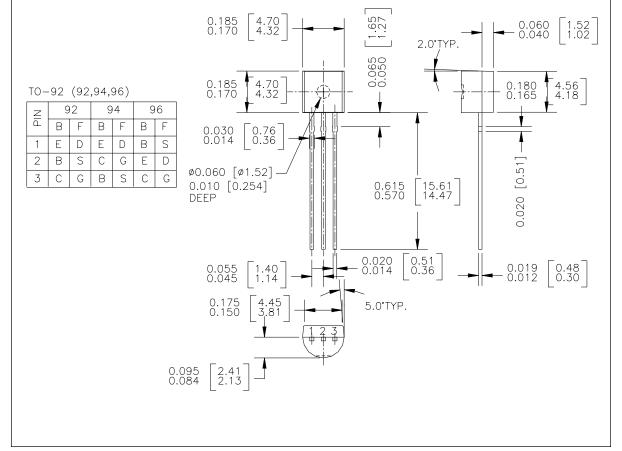
TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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DOME™ ISOPLANAR™ Quiet Series™
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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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